**Amendments to the Claims**

Please amend Claim 15. The Claim Listing below will replace all prior versions of the claims in the application:

**Claim Listing**

1. (Original) A method of forming an epitaxial film on a substrate, comprising the steps of:
   (a) growing an initial layer of a film on a substrate at a temperature $T_{growth}$, said initial layer having a thickness $h$;
   (b) annealing the initial layer of the film at a temperature $T_{anneal}$, thereby substantially completely relaxing the initial layer.

2. (Original) The method of Claim 1 further including growing additional layers of the film over the initial layer subsequent to annealing.

3. (Original) The method of Claim 1 wherein said thickness $h$ of the initial layer of the film is greater than a critical thickness $h_c$.

4. (Original) The method of Claim 1 wherein $h$ between about 1 and about 5 monolayers.

5. (Original) The method of Claim 1 wherein $T_{growth}$ is about equal to $T_{anneal}$.

6. (Original) The method of Claim 1 wherein $T_{growth}$ is less than $T_{anneal}$.

7. (Original) The method of Claim 1 wherein growth of the initial layer includes two-dimensional growth.

8. (Original) The method of Claim 1 wherein the substrate includes Si(100) and the film includes TiN.

9. (Original) The method of Claim 1 wherein the substrate includes Si(111) and the film includes at least one III-nitride selected from the group consisting of AlN, GaInN, and AlGaInN.

10. (Original) The method of Claim 9 wherein the film includes AlN.

11. (Original) The method of Claim 1 wherein the substrate includes $Al_2O_3$(0001) and wherein the film includes at least one member selected from the group consisting of ZnO, AlN, GaInN, and AlGaInN.

12. (Original) The method of Claim 11 wherein the film includes ZnO.

13. (Original) The method of Claim 2 further including the step of growing a layer of the film that includes at least one amorphous area.

14. (Original) The method of Claim 14 wherein at least one amorphous area includes Si.

15. (Currently amended) The method of Claim 14 wherein at least one area of amorphous growth includes ~~silicone~~ silicon nitride or ~~silicone~~ silicon oxide.